

M57916L

HYBRID IC FOR DRIVING TRANSISTOR MODULES

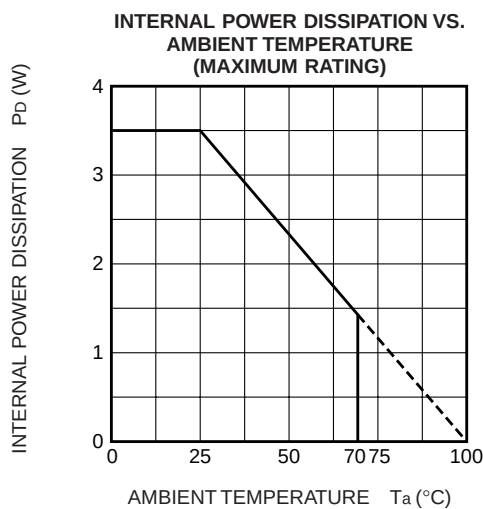
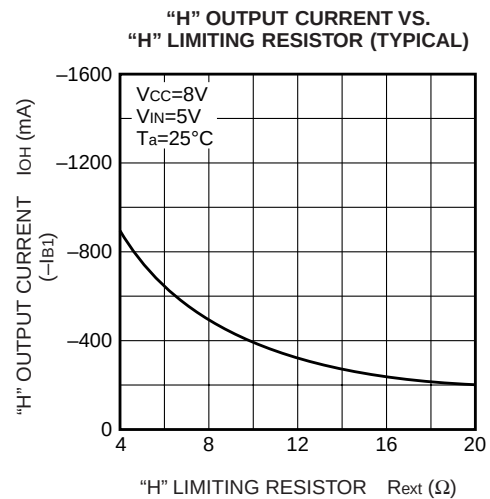
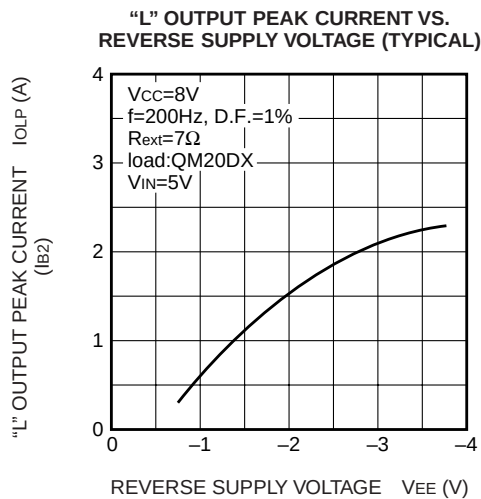
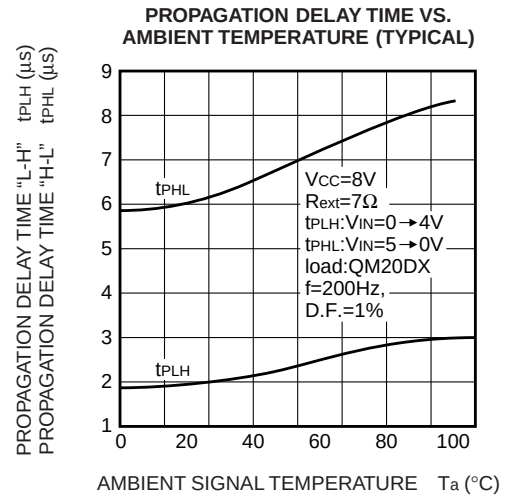
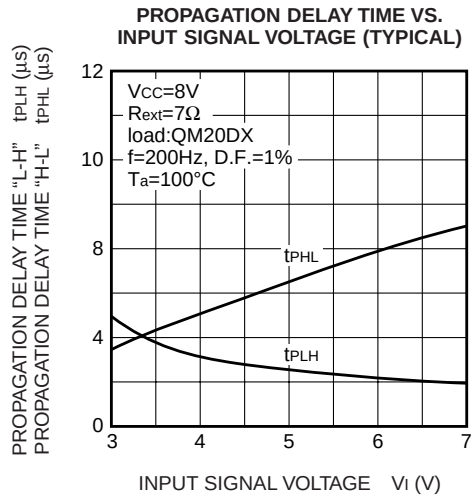
ABSOLUTE MAXIMUM RATINGS (Ta=-20 ~ +70°C, unless otherwise noted)

Symbol	Parameter	Conditions	Ratings	Unit
V _{CC}	Supply voltage	DC	14	V
V _I	Input voltage	Between terminals ① and ②	-1 ~ 7	V
I _{OH}	Output current		-1	A
I _{OLP}		Pulse width 10μs, Freq. 2kHz, peak value	3	A
V _{iso}	Isolation voltage between two currents	Sinewave voltage 60Hz/min. Ta=25°C	2500	V _{rms}
T _j	Junction temperature		100	°C
T _{opg}	Operating temperature		-20 ~ +70	°C
T _{stg}	Storage temperature		-25 ~ +100	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, V_{CC}=8V, unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
I _{IH}	"H" input current	V _I =5V	-	7	-	mA
I _{OH}	"H" output current	R _{ext} =7Ω	-	-0.5	-	A
I _{OLP}	"L" output peak current	C _{ext} =47μF	-	1	-	A
P _D	Internal power dissipation	I _{OH} =-0.5A, I _{OLP} =1A, f=2kHz, D.F.=50%	-	1.25	-	W
t _{PLH}	"L-H" propagation delay time	V _I =0→4V, T _j =100°C	-	5	10	μs
t _{PHL}	"H-L" propagation delay time	V _I =5→0V, T _j =100°C	-	8	15	μs

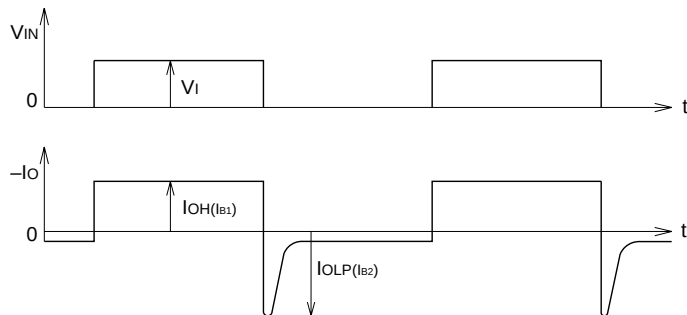
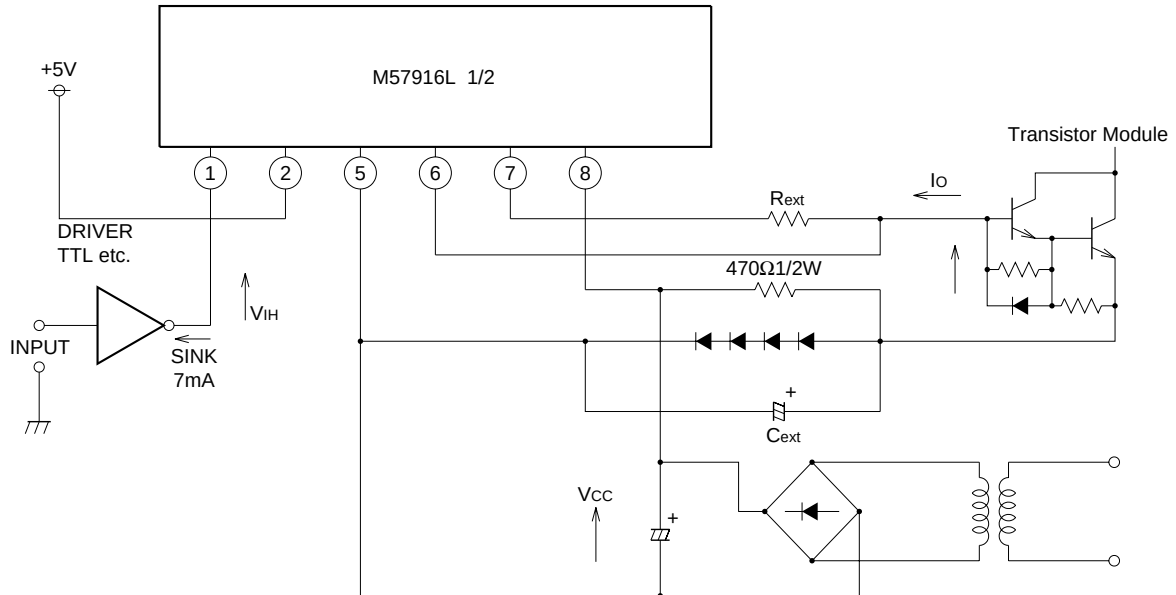
PERFORMANCE CURVES



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TEST CIRCUIT AND APPLICATION CIRCUIT EXAMPLE



Note: IOH and IOLP correspond to base forward current IB1 and base reverse current IB2 of the transistor module to be driven respectively.